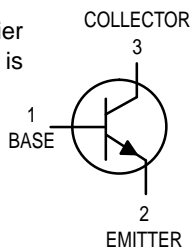


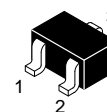
# General Purpose Transistors

## NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-323/SC-70 which is designed for low power surface mount applications.



**BC846AWT1,BWT1**  
**BC847AWT1,BWT1,**  
**CWT1**  
**BC848AWT1,BWT1,**  
**CWT1**



CASE 419-02, STYLE 3  
SOT-323/SC-70

### MAXIMUM RATINGS

Rating	Symbol	BC846	BC847	BC848	Unit
Collector–Emitter Voltage	$V_{CEO}$	65	45	30	V
Collector–Base Voltage	$V_{CBO}$	80	50	30	V
Emitter–Base Voltage	$V_{EBO}$	6.0	6.0	5.0	V
Collector Current — Continuous	$I_C$	100	100	100	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A = 25^\circ\text{C}$	$P_D$	150	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Total Device Dissipation	$P_D$	2.4	$\text{mW}/^\circ\text{C}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

### DEVICE MARKING

BC846AWT1 = 1A; BC846BWT1 = 1B; BC847AWT1 = 1E; BC847BWT1 = 1F;  
BC847CWT1 = 1G; BC848AWT1 = 1J; BC848BWT1 = 1K; BC848CWT1 = 1L

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector–Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ )	$V_{(BR)CEO}$	65 45 30	— — —	— — —	V
Collector–Emitter Breakdown Voltage ( $I_C = 10\ \mu\text{A}, V_{EB} = 0$ )	$V_{(BR)CES}$	80 50 30	— — —	— — —	V
Collector–Base Breakdown Voltage ( $I_C = 10\ \mu\text{A}$ )	$V_{(BR)CBO}$	80 50 30	— — —	— — —	V
Emitter–Base Breakdown Voltage ( $I_E = 1.0\ \mu\text{A}$ )	$V_{(BR)EBO}$	6.0 6.0 5.0	— — —	— — —	V
Collector Cutoff Current ( $V_{CB} = 30\text{ V}$ ) ( $V_{CB} = 30\text{ V}, T_A = 150^\circ\text{C}$ )	$I_{CBO}$	— —	— —	15 5.0	nA $\mu\text{A}$

1. FR-5 = 1.0 x 0.75 x 0.062 in

Thermal Clad is a trademark of the Bergquist Company.

# BC846AWT1,BWT1 BC847AWT1,BWT1,CWT1 BC848AWT1,BWT1,CWT1

ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$  unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = 10\ \mu\text{A}$ , $V_{CE} = 5.0\ \text{V}$ )	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C	$h_{FE}$	— — —	90 150 270	— — —
( $I_C = 2.0\ \text{mA}$ , $V_{CE} = 5.0\ \text{V}$ )	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C		110 200 420	180 290 520	220 450 800
Collector–Emitter Saturation Voltage ( $I_C = 10\ \text{mA}$ , $I_B = 0.5\ \text{mA}$ ) ( $I_C = 100\ \text{mA}$ , $I_B = 5.0\ \text{mA}$ )		$V_{CE(sat)}$	— —	— —	0.25 0.6
Base–Emitter Saturation Voltage ( $I_C = 10\ \text{mA}$ , $I_B = 0.5\ \text{mA}$ ) ( $I_C = 100\ \text{mA}$ , $I_B = 5.0\ \text{mA}$ )		$V_{BE(sat)}$	— —	0.7 0.9	— —
Base–Emitter Voltage ( $I_C = 2.0\ \text{mA}$ , $V_{CE} = 5.0\ \text{V}$ ) ( $I_C = 10\ \text{mA}$ , $V_{CE} = 5.0\ \text{V}$ )		$V_{BE(on)}$	580 —	660 —	700 770

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ( $I_C = 10\ \text{mA}$ , $V_{CE} = 5.0\ \text{Vdc}$ , $f = 100\ \text{MHz}$ )		$f_T$	100	—	—	MHz
Output Capacitance ( $V_{CB} = 10\ \text{V}$ , $f = 1.0\ \text{MHz}$ )		$C_{obo}$	—	—	4.5	pF
Noise Figure ( $I_C = 0.2\ \text{mA}$ , $V_{CE} = 5.0\ \text{Vdc}$ , $R_S = 2.0\ \text{k}\Omega$ , $f = 1.0\ \text{kHz}$ , $BW = 200\ \text{Hz}$ )	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C	NF	— — —	— — —	10 4.0	dB

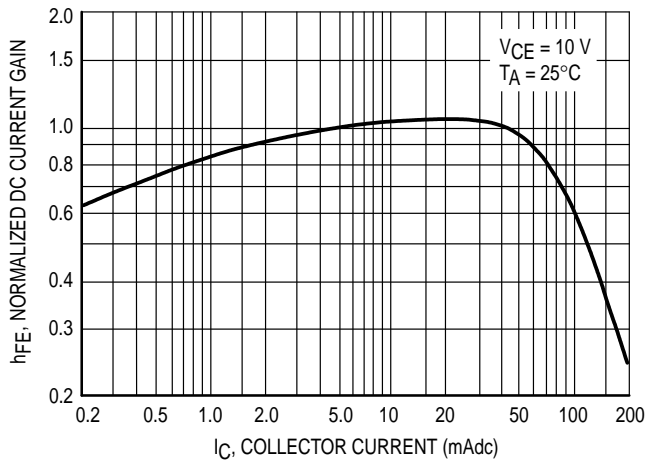


Figure 1. Normalized DC Current Gain

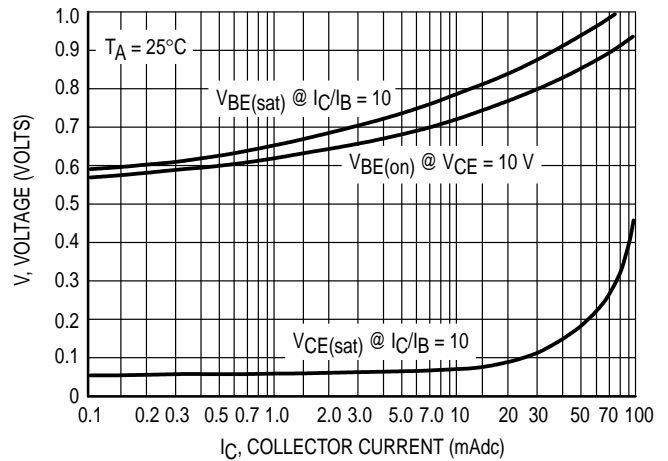


Figure 2. "Saturation" and "On" Voltages

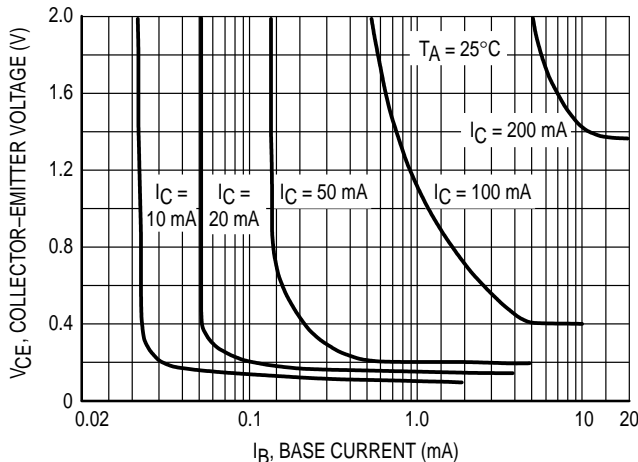


Figure 3. Collector Saturation Region

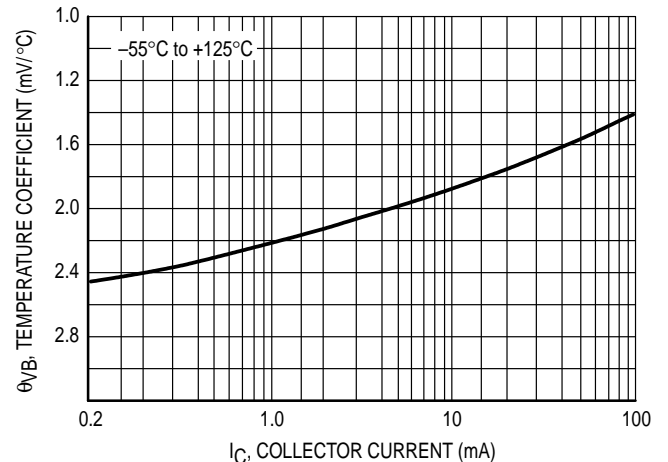
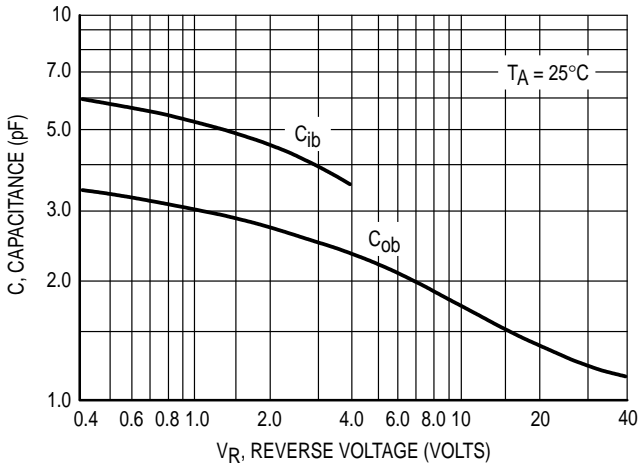
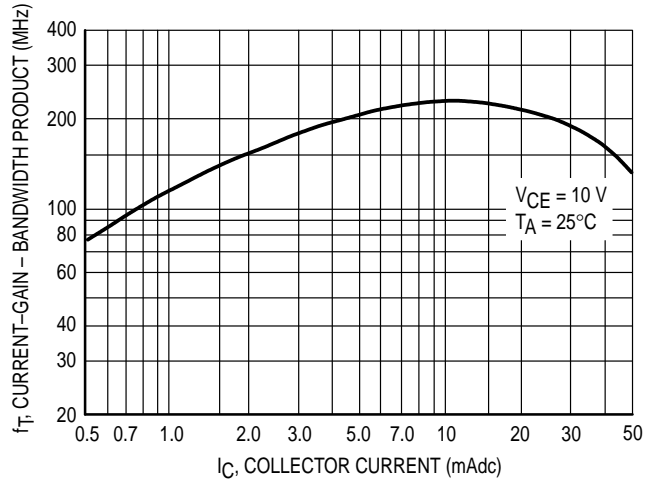


Figure 4. Base–Emitter Temperature Coefficient

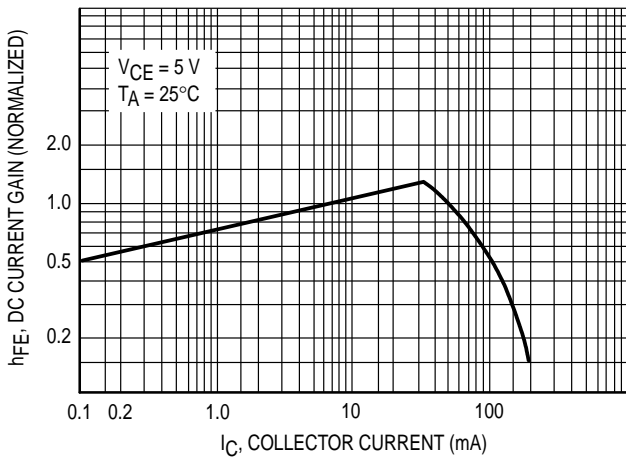
**BC846AWT1,BWT1 BC847AWT1,BWT1,CWT1 BC848AWT1,BWT1,CWT1  
BC847/BC848**



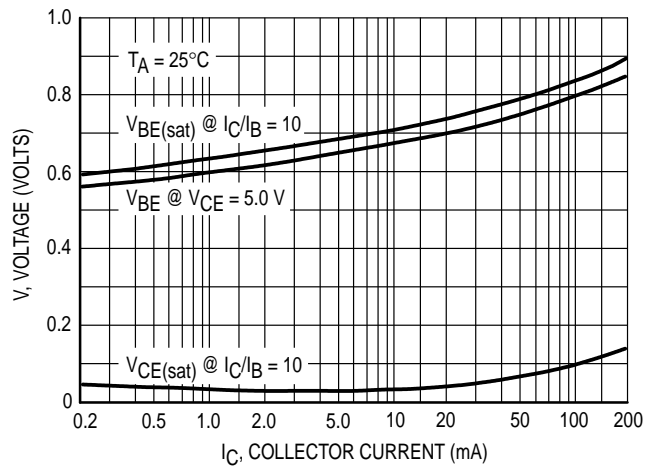
**Figure 5. Capacitances**



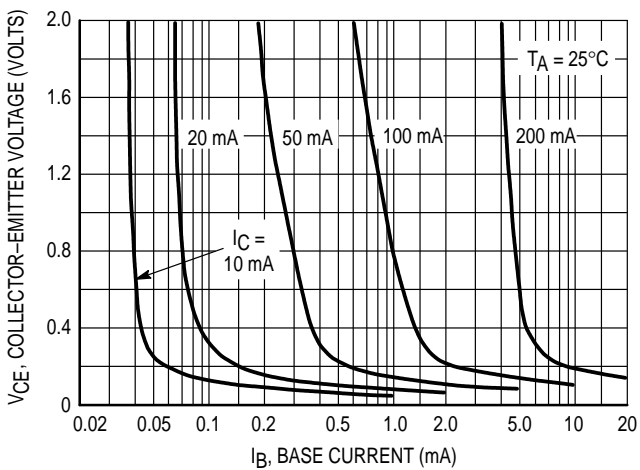
**Figure 6. Current-Gain - Bandwidth Product**



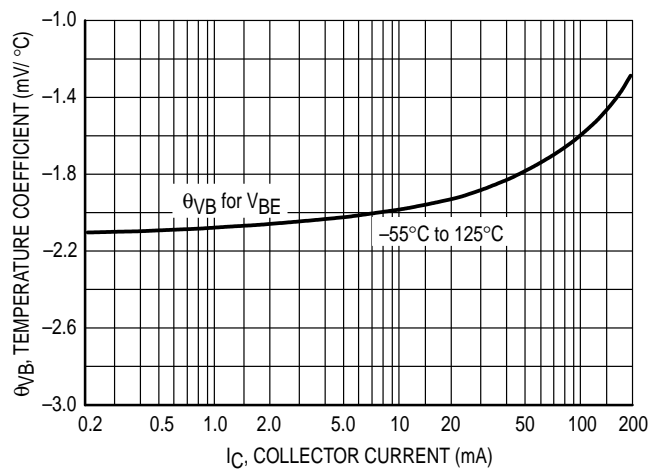
**Figure 7. DC Current Gain**



**Figure 8. "On" Voltage**



**Figure 9. Collector Saturation Region**



**Figure 10. Base-Emitter Temperature Coefficient**

BC846

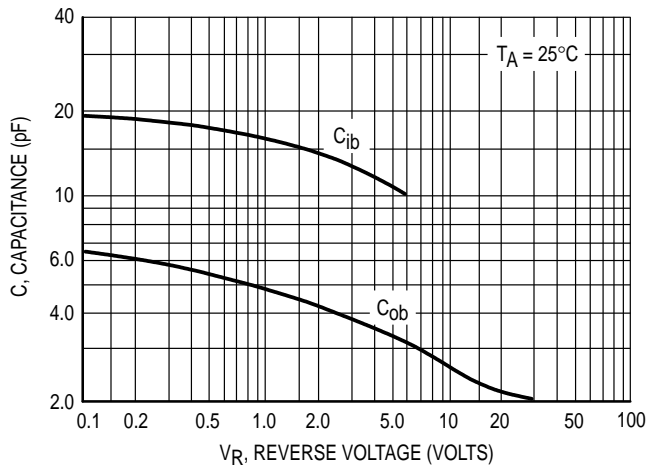


Figure 11. Capacitance

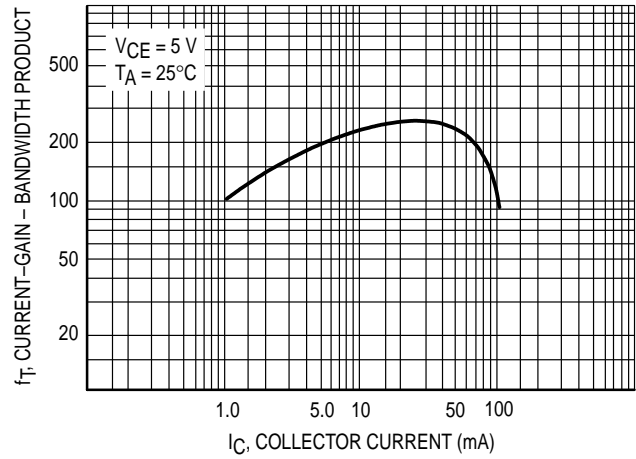


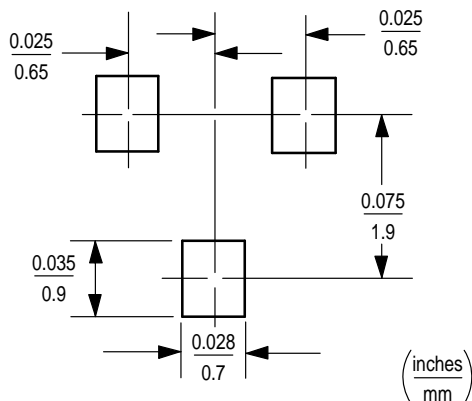
Figure 12. Current-Gain - Bandwidth Product

## INFORMATION FOR USING THE SOT-323/SC-70 SURFACE MOUNT PACKAGE

### MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



SOT-323/SC-70

### SOT-323/SC-70 POWER DISSIPATION

The power dissipation of the SOT-323/SC-70 is a function of the pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by  $T_{J(max)}$ , the maximum rated junction temperature of the die,  $R_{\theta JA}$ , the thermal resistance from the device junction to ambient, and the operating temperature,  $T_A$ . Using the values provided on the data sheet for the SOT-323/SC-70 package,  $P_D$  can be calculated as follows:

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature  $T_A$  of 25°C, one can calculate the power dissipation of the device which in this case is 150 milliwatts.

$$P_D = \frac{150^\circ\text{C} - 25^\circ\text{C}}{833^\circ\text{C/W}} = 150 \text{ milliwatts}$$

The 833°C/W for the SOT-323/SC-70 package assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 150 milliwatts. There are other alternatives to achieving higher power dissipation from the SOT-323/SC-70 package. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad™. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

### SOLDERING PRECAUTIONS

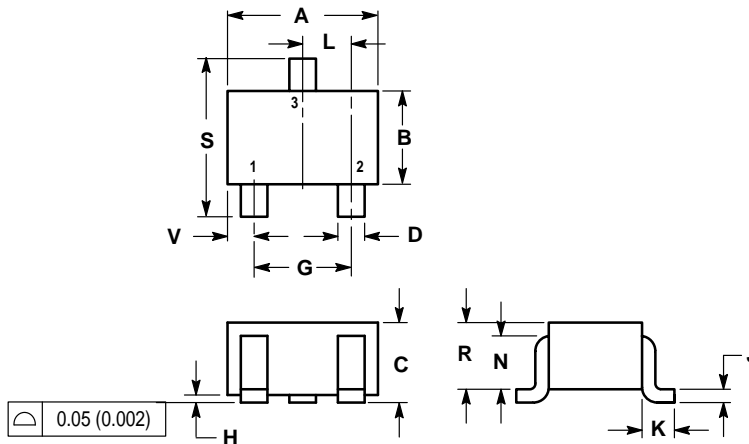
The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.\*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference shall be a maximum of 10°C.
- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient shall be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.

\* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

**BC846AWT1,BWT1 BC847AWT1,BWT1,CWT1 BC848AWT1,BWT1,CWT1**

**PACKAGE DIMENSIONS**



- NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.035	0.049	0.90	1.25
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
R	0.031	0.039	0.80	1.00
S	0.079	0.087	2.00	2.20
V	0.012	0.016	0.30	0.40

- STYLE 3:  
 PIN 1. BASE  
 2. EMITTER  
 3. COLLECTOR

**CASE 419-02  
 ISSUE G  
 SOT-323/SC-70**

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